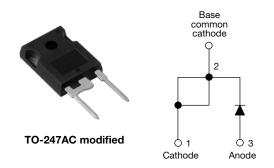
Vishay High Power Products

HEXFRED[®] Ultrafast Soft Recovery Diode, 15 A



PRODUCT SUMMARY				
V _R	600 V			
V _F at 15 A at 25 °C	1.7 V			
I _{F(AV)}	15 A			
t _{rr} (typical)	19 ns			
T _J (maximum)	150 °C			
Q _{rr} (typical)	80 nC			
dl _{(rec)M} /dt (typical) at 125 °C	160 A/µs			
I _{RRM} (typical)	4.0 A			

FEATURES

- Ultrafast recovery
- Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating conditions
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

HFA15PB60 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 15 A continuous current, the HFA15PB60 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA15PB60 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V _R		600	V	
Maximum continuous forward current	١ _F	T _C = 100 °C	15		
Single pulse forward current	I _{FSM}		150	А	
Maximum repetitive forward current	I _{FRM}		60		
Maximum neuror dissinction	P _D	T _C = 25 °C	74	10/	
Maximum power dissipation		T _C = 100 °C	29	- W	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

* Pb containing terminations are not RoHS compliant, exemptions may apply



HFA15PB60PbF

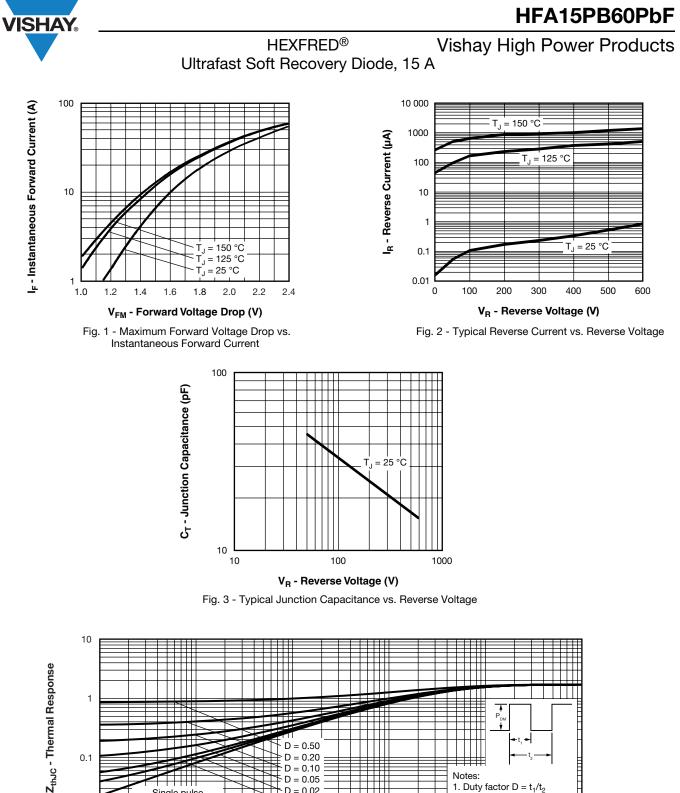


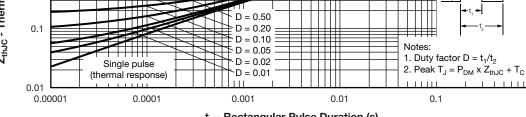
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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA		600	-	-	
Maximum forward voltage V _{FM}		I _F = 15 A	See fig. 1	-	1.3	1.7	V
	V _{FM}	I _F = 30 A		-	1.5	2.0	
	I _F = 15 A, T _J = 125 °C	-		1.2	1.6		
Maximum reverse I _{RM}	$V_R = V_R$ rated	See fig. 2 -	-	1.0	10	μA	
	T_J = 125 °C, V_R = 0.8 x V_R rated		-	400	1000		
Junction capacitance	CT	V _R = 200 V	See fig. 3	-	25	50	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 12		12	-	nH	

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5, 10	t _{rr}	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$		-	19	-	
	t _{rr1}	T _J = 25 °C		-	42	60	ns
	t _{rr2}	T _J = 125 °C		-	74	120	
Peak recovery current See fig. 6	I _{RRM1}	T _J = 25 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 200 V	-	4.0	6.0	A nC
	I _{RRM2}	T _J = 125 °C		-	6.5	10	
Reverse recovery charge See fig. 7	Q _{rr1}	T _J = 25 °C		-	80	180	
	Q _{rr2}	T _J = 125 °C		-	220	600	
Peak rate of fall of recovery current during t _b See fig. 8	dl _{(rec)M} /dt1	T _J = 25 °C		-	188	-	− A/µs
	dl _{(rec)M} /dt2	T _J = 125 °C		-	160	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-	
Weight			-	6.0	-	g
weight			-	0.21	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)	HFA15PB60			





t₁ - Rectangular Pulse Duration (s)

Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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HFA15PB60PbF

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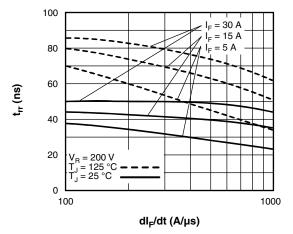


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

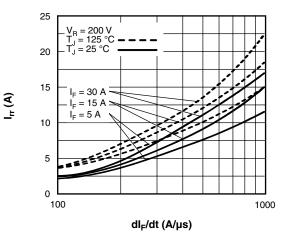


Fig. 6 - Typical Recovery Current vs. dl_F/dt

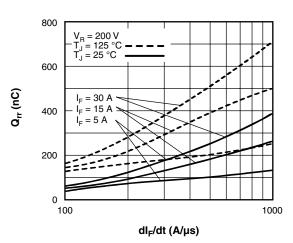


Fig. 7 - Typical Stored Charge vs. dl_F/dt

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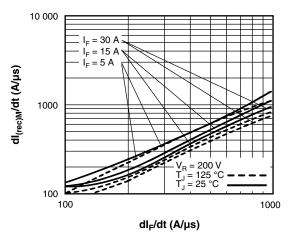


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt



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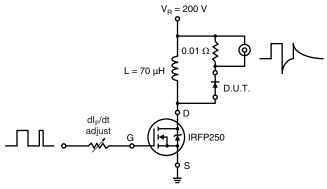
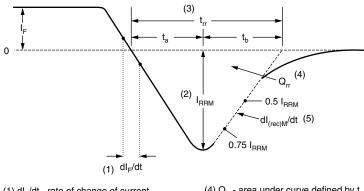


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and $I_{\rm RBM}$

I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{F}}{2}$$

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing

through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(2) I_{RRM} - peak reverse recovery current

- (5) dI_{(rec)M}/dt peak rate of change of current during t_b portion of t_{rr}
- Fig. 10 Reverse Recovery Waveform and Definitions

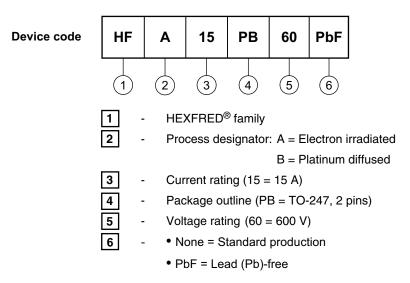
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ORDERING INFORMATION TABLE



LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95253					
Part marking information	www.vishay.com/doc?95255				



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